

# 4V Drive Nch+Nch MOSFET

# **SH8K22**

# **●Structure**

Silicon N-channel MOSFET

#### Features

- 1) Built-in G-S Protection Diode.
- 2) Small surface Mount Package (SOP8).

#### Application

Power switching, DC / DC converter, Inverter

### Packaging specifications

Туре	Package	Taping		
	Code	TB		
	Basic ordering unit (pieces)	2500		
SH8K22		0		

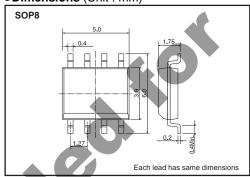
# ●Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2.>

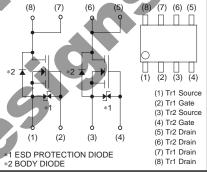
Parameter		Symbol	Limits	Unit		
Drain-source voltage		$V_{DSS}$	45	V		
Gate-source voltage		$V_{GSS}$	±20	V		
Drain current	Continuous	<u>_</u>	±4.5	Α		
	Pulsed	I <sub>DP</sub> *1	±18	Α		
Source current (Body diode)	Continuous	Is	1	А		
	Pulsed	I <sub>SP</sub> *1	18	А		
Total power dissipation		P <sub>D *2</sub>	2	W / TOTAL		
		FD *2	1.4	W / ELEMENT		
Chanel temperature		$T_{ch}$	150	°C		
Range of Storage temperature		T <sub>stg</sub>	-55 to +150	°C		
14 714						

<sup>\*1</sup> PW  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

#### ●Dimensions (Unit: mm)



#### Inner circuit



A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

<sup>\*2</sup> Mounted on a ceramic board

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#### ●Electrical characteristics (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	_	_	±10	μΑ	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)</sub> DSS	45	-	-	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	_	_	1	μА	Vps= 45V, Vgs=0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	_	2.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state resistance		-	33	46	mΩ	I <sub>D</sub> = 4.5A, V <sub>GS</sub> = 10V
	R <sub>DS (on)</sub> *	-	41	57	mΩ	I <sub>D</sub> = 4.5A, V <sub>GS</sub> = 4.5V
		-	46	64	mΩ	Ip= 4.5A, Vgs= 4.0V
Forward transfer admittance	Y <sub>fs</sub> *	3.5	_	-	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 4.5A
Input capacitance	Ciss	-	550	_	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	-	140	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	-	70	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	12	-	ns	V <sub>DD</sub> ≒ 25V
Rise time	tr *	-	18	_	ns	ID= 2.5A
Turn-off delay time	t <sub>d (off)</sub> *	-	42	-	ns	V <sub>GS</sub> = 10V R <sub>L</sub> = 10Ω
Fall time	t <sub>f</sub> *	-	12	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	-	6.8	9.6	nC	V <sub>DD</sub> ≒25V, V <sub>GS</sub> =5V
Gate-source charge	Q <sub>gs</sub> *	-	2.0	-	nC	I <sub>D</sub> = 4.5A
Gate-drain charge	Q <sub>gd</sub> *	_	2.9	_	nC	$R_L=5.6\Omega$ , $R_G=10\Omega$
::Dulaad						

<sup>\*</sup>Pulsed

# ●Body diode characteristics (Source-Drain) (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

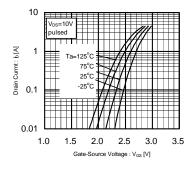
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
Forward voltage	V <sub>SD</sub> *	-	_	1.2	V	$I_S=4.5A/V_{GS}=0V$	

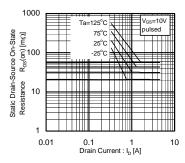
<sup>\*</sup> pulsed



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#### •Electrical characteristic curves





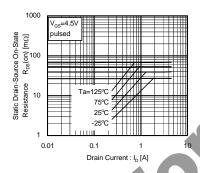
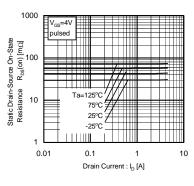
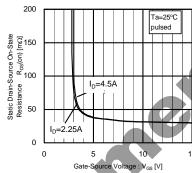


Fig.1 Typical Transfer Characteristics

Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (1)

Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (2)





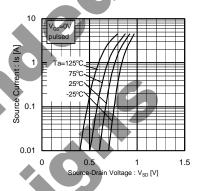
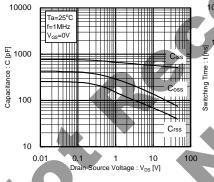
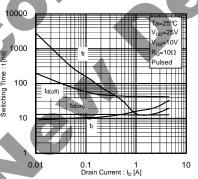


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (3)

Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

Fig.6 Source-Current vs. Source-Drain Voltage





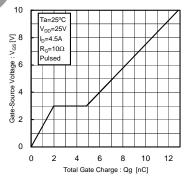


Fig.7 Typical capacitance vs. Source-Drain Voltage

Fig.8 Switching Characteristics

Fig.9 Dynamic Input Characteristics

**Data Sheet SH8K22** 

#### Measurement circuits

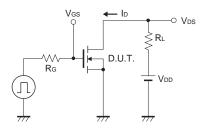


Fig.10 Switching Time Test Circuit

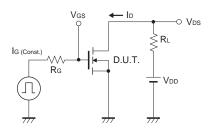


Fig.12 Gate Charge Test Circuit

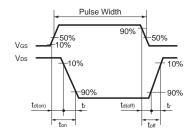
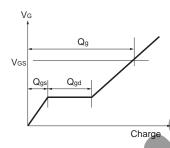


Fig.11 Switching Time Waveforms





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